N-Channel 25-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a, e]	Q_g (Typ)
25	0.0052 @ V_{GS} = 10 V	89	30 nC
	0.0076 @ V_{GS} = 4.5 V	80	

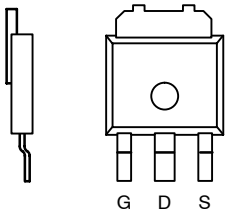
FEATURES

- TrenchFET® Power MOSFET
- 100% R_g Tested
- RoHS Compliant

APPLICATIONS

- DC/DC Conversion, Low-Side
  - Desktop PC
  - Notebook PC

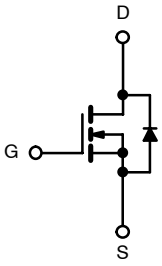
TO-252
Reverse Lead DPAK



Drain Connected to Tab

Top View

Ordering Information:
SUR50N025-05P—E3 (Lead (Pb)-Free)
SUR50N025-05P-T4—E3 (Lead (Pb)-Free, alternate tape orientation)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	25	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175°C)	T_C = 25°C	I_D	89[a, e]	A
	T_C = 70°C		75[a, e]	
	T_A = 25°C		36[b, c]	
	T_A = 70°C		30[b, c]	
Pulsed Drain Current		I_{DM}	100	
Continuous Source-Drain Diode Current	T_C = 25°C	I_S	55	
	T_A = 25°C		7.7[b, c]	
Avalanche Current Pulse	L = 0.1 mH	I_{AS}	45	
Single Pulse Avalanche Energy		E_{AS}	101	mJ
Maximum Power Dissipation	T_C = 25°C	P_D	83[a]	W
	T_C = 70°C		58[a]	
	T_A = 25°C		11.5[b, c]	
	T_A = 70°C		8.0[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 10 sec	R_{thJA}	10	13	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	1.5	1.8	

Notes:
a. Based on T_C = 25°C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 sec
d. Maximum under steady state conditions is 90 °C/W.
e. Calculated based on maximum junction temperature. Package limitation current is 50 A.

SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

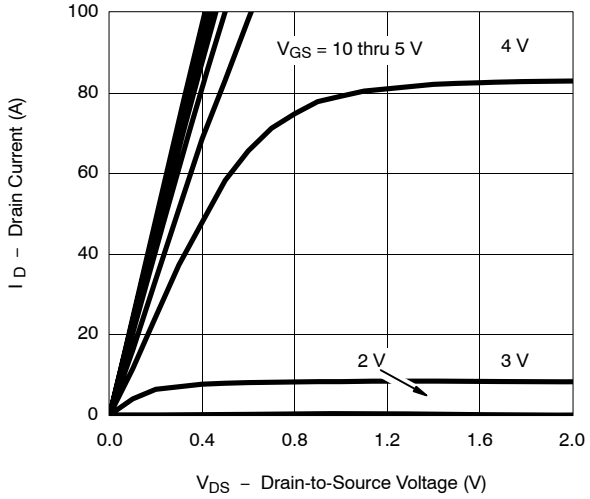
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	25			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 μA		20		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			–6.0		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	1.4		2.4	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 25 V, V_{GS} = 0 V			1	μA
		V_{DS} = 25 V, V_{GS} = 0 V, T_J = 55°C			10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	50			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.0042	0.0052	Ω
		V_{GS} = 4.5 V, I_D = 15 A		0.0062	0.0076	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 15 A		65		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 12 V, V_{GS} = 0 V, f = 1 MHz		3600		pF
Output Capacitance	C_{oss}			790		
Reverse Transfer Capacitance	C_{rss}			430		
Total Gate Charge	Q_g	V_{DS} = 12 V, V_{GS} = 10 V, I_D = 50 A		63	95	nC
		V_{DS} = 12 V, V_{GS} = 4.5 V, I_D = 50 A		30	45	
Gate-Source Charge	Q_{gs}			10.5		
Gate-Drain Charge	Q_{gd}			10.5		
Gate Resistance	R_g	f = 1 MHz	0.5	1.0	1.5	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 12 V, R_L = 0.24 Ω I_D ≅ 50 A, V_{GEN} = 4.5 V, R_g = 1 Ω		24	36	ns
Rise Time	t_r			13	20	
Turn-Off Delay Time	$t_{d(off)}$			24	36	
Fall Time	t_f			7.5	12	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 12 V, R_L = 0.24 Ω I_D ≅ 50 A, V_{GEN} = 10 V, R_g = 1 Ω		11	17	
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(off)}$			29	44	
Fall Time	t_f			8	12	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25°C			55	A
Pulse Diode Forward Current[a]	I_{SM}				100	
Body Diode Voltage	V_{SD}	I_S = 30 A		0.9	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 20 A, di/dt = 100 A/μs, T_J = 25°C		34	51	ns
Body Diode Reverse Recovery Charge	Q_{rr}			25	38	nC
Reverse Recovery Fall Time	t_a			17		ns
Reverse Recovery Rise Time	t_b			17		

Notes
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

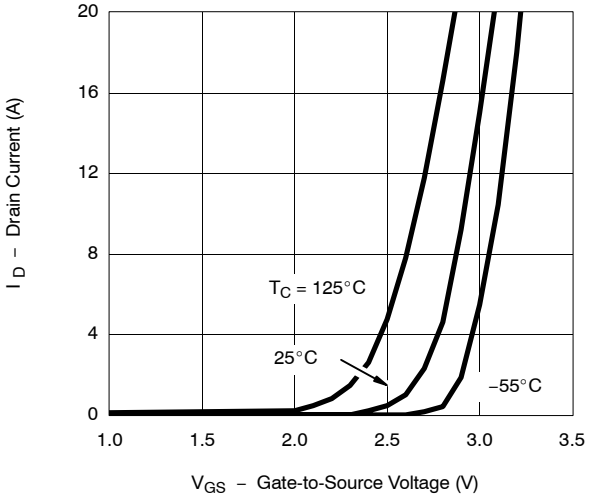
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

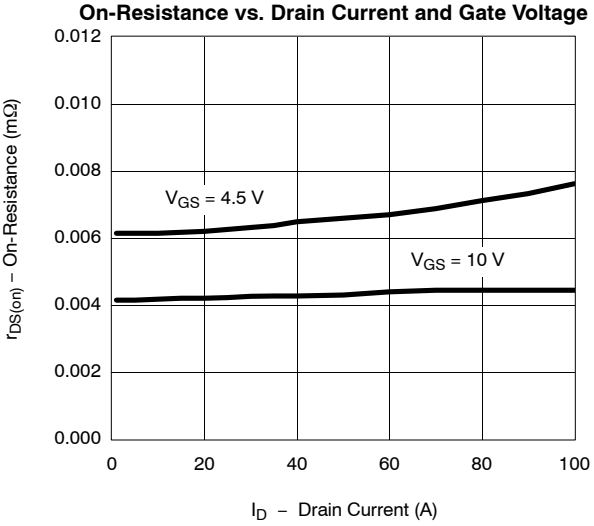
Output Characteristics



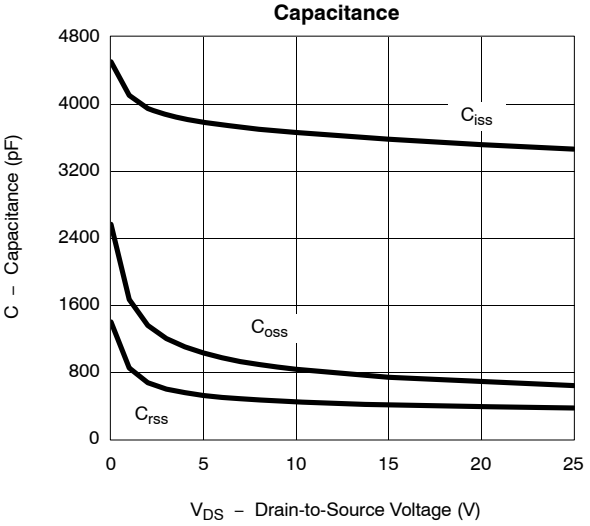
Transfer Characteristics



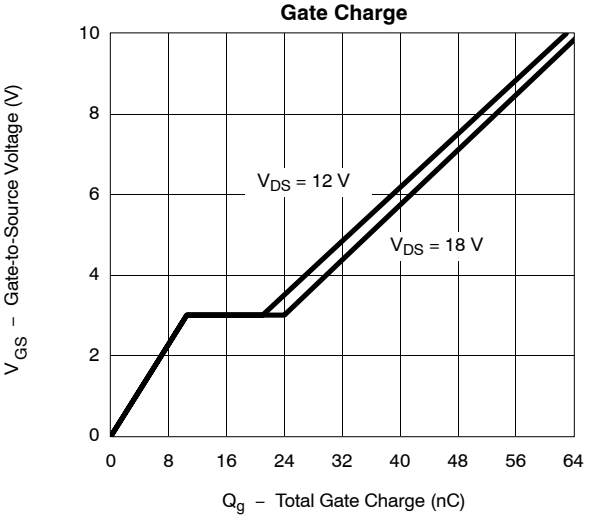
On-Resistance vs. Drain Current and Gate Voltage



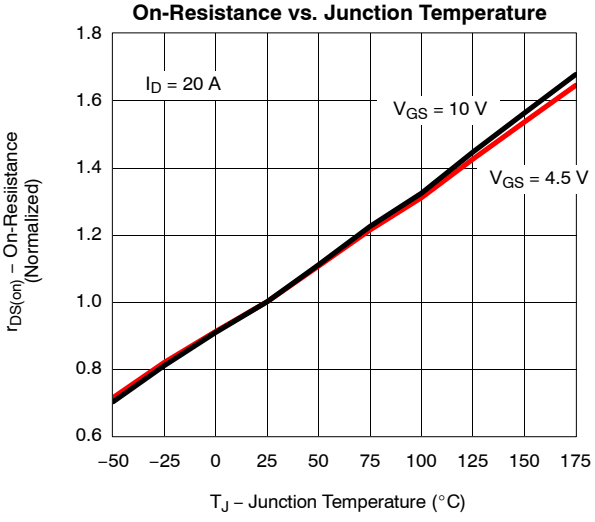
Capacitance



Gate Charge

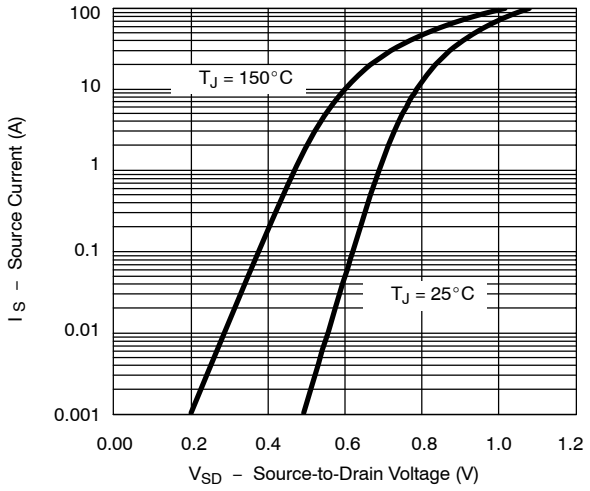


On-Resistance vs. Junction Temperature

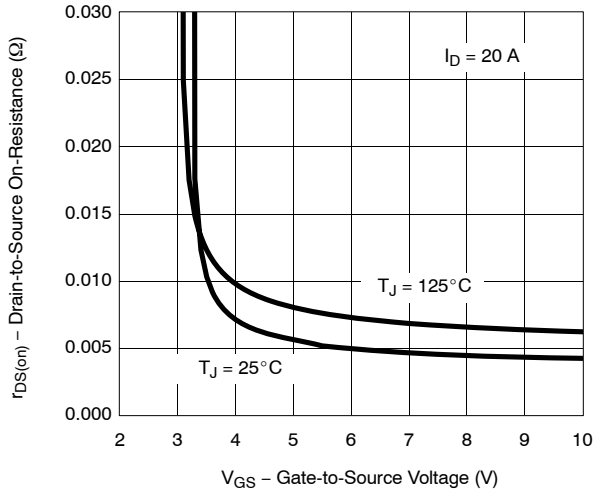


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

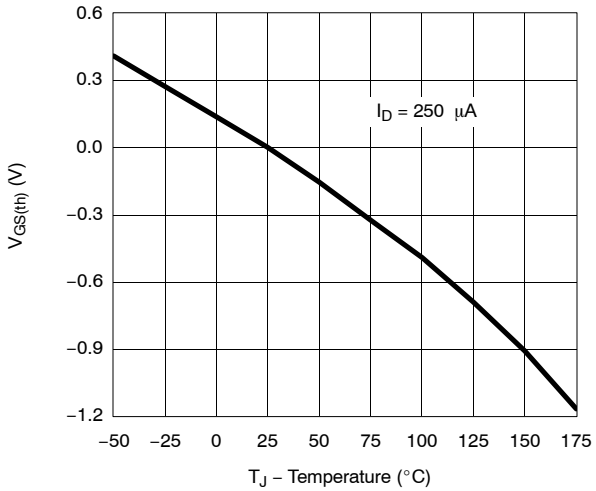
Source-Drain Diode Forward Voltage



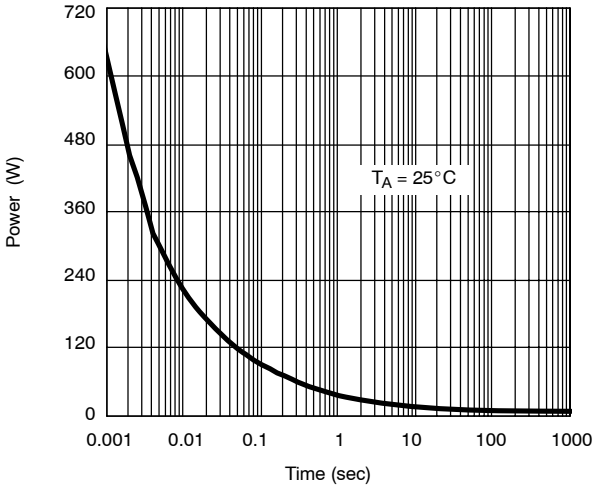
On-Resistance vs. Gate-to-Source Voltage



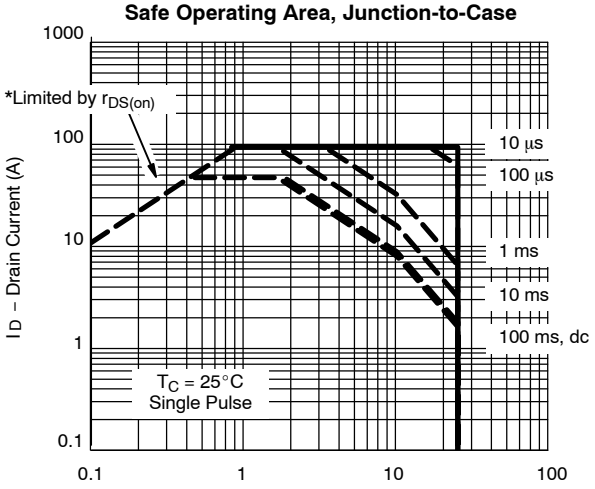
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

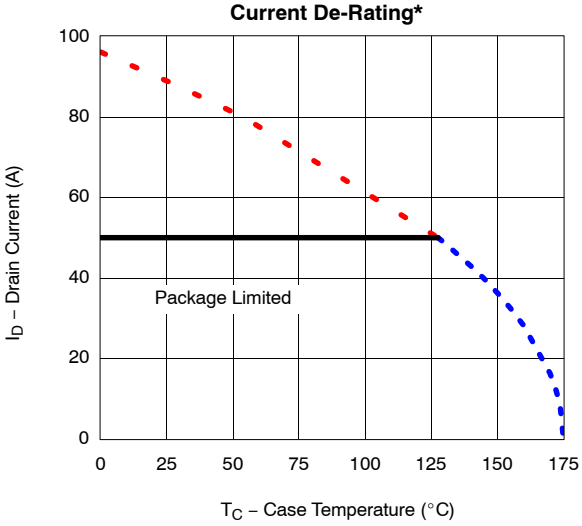


Safe Operating Area, Junction-to-Case

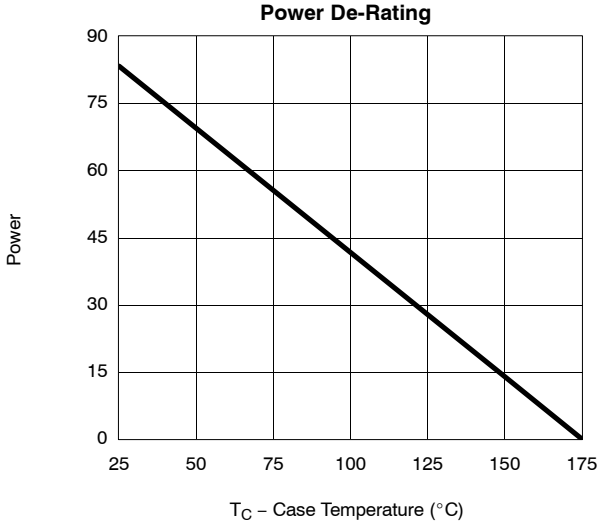


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

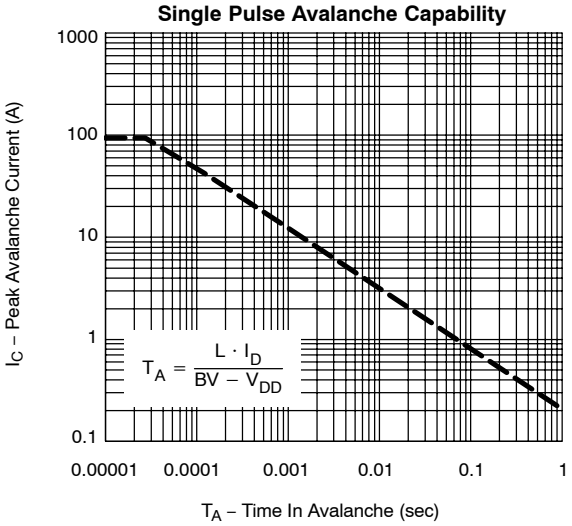
Current De-Rating*



Power De-Rating

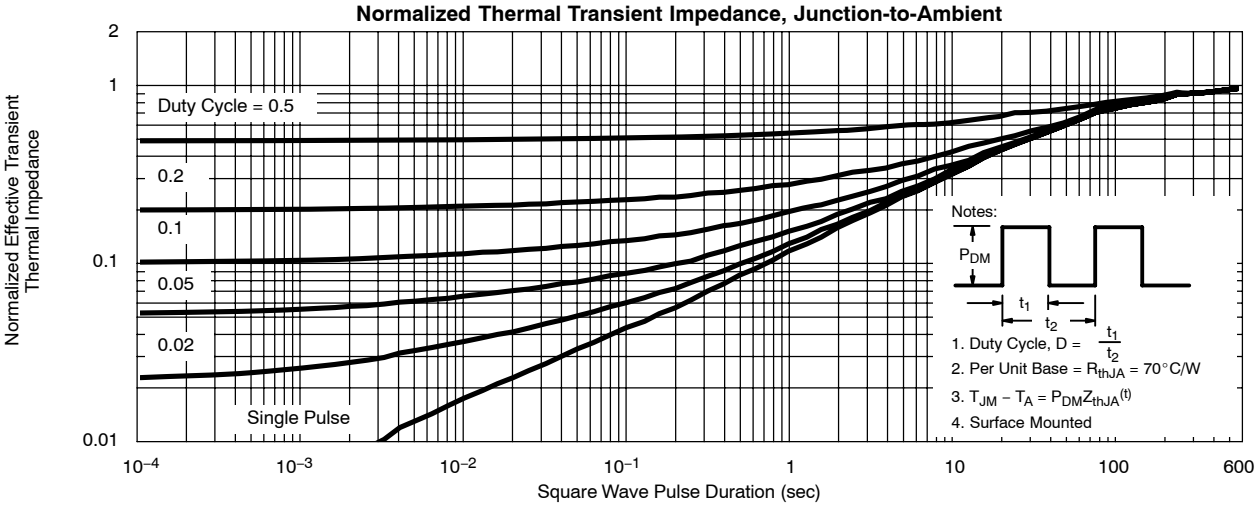


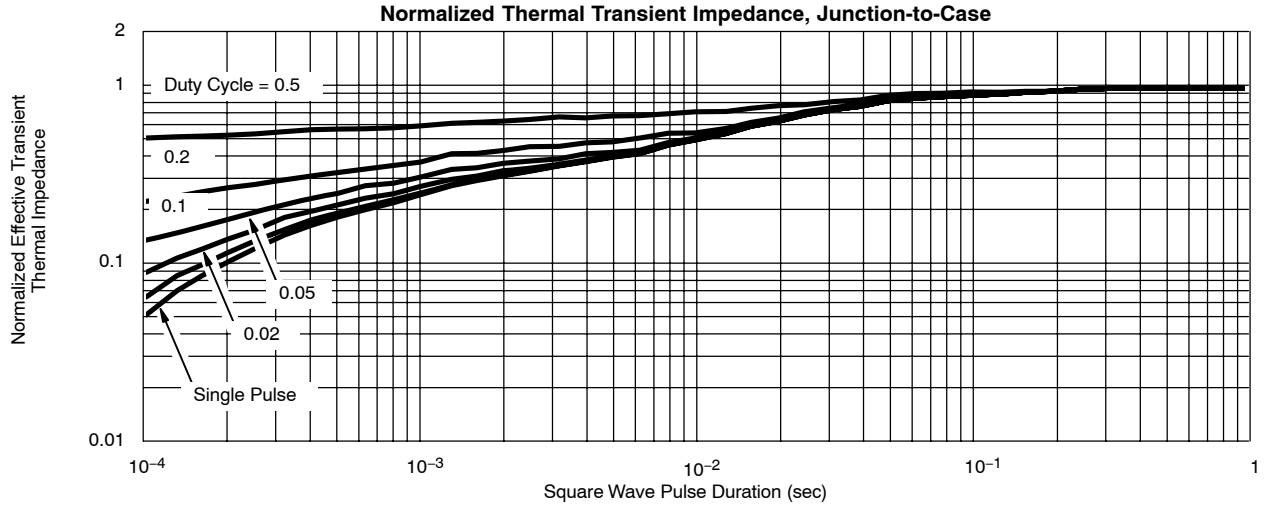
Single Pulse Avalanche Capability



*The power dissipation P_D is based on $T_{J(max)}$ = 175°C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





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